

PJQ4463AP-AU

60V P-Channel Enhancement Mode MOSFET

Voltage

-60 V

Current

-4.2 A

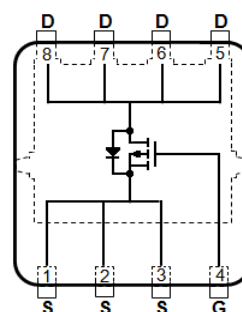
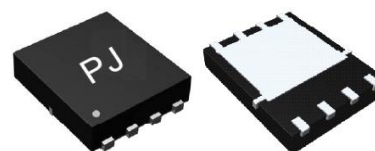
Features

- $R_{DS(ON)}$, $V_{GS}@-10V$, $I_D@-6A < 68m\Omega$
- $R_{DS(ON)}$, $V_{GS}@-4.5V$, $I_D@-3A < 85m\Omega$
- Advanced Trench Process Technology
- High density cell design for ultra low on-resistance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case : DFN3333-8L Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.001 ounces, 0.03 grams

DFN3333-8L



Maximum Ratings and Thermal Characteristics ($T_A=25^{\circ}C$ unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V_{DS}	-60	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (Note 4)	$T_A=25^{\circ}C$	I_D	-4.2	A
	$T_A=70^{\circ}C$		-3.4	
Pulsed Drain Current (Note 1)		I_{DM}	-16.8	
Power Dissipation	$T_A=25^{\circ}C$	P_D	2.1	W
	$T_A=70^{\circ}C$		1.3	
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~150	$^{\circ}C$
Typical Thermal Resistance Junction to Ambient (Note 4,5)		$R_{\theta JA}$	59.5	$^{\circ}C/W$

- Limited only By Maximum Junction Temperature



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Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250uA	-60	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250uA	-1	-1.53	-2.5	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-6A	-	55	68	mΩ
		V _{GS} =-4.5V, I _D =-3A	-	71	85	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-60V, V _{GS} =0V	-	-	-1	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
Dynamic (Note 6)						
Total Gate Charge	Q _g	V _{DS} =-30V, I _D =-6A, V _{GS} =-10V (Note 3)	-	17	-	nC
Gate-Source Charge	Q _{gs}		-	2.8	-	
Gate-Drain Charge	Q _{gd}		-	3.6	-	
Input Capacitance	C _{iss}	V _{DS} =-30V, V _{GS} =0V, f=1MHZ	-	879	-	pF
Output Capacitance	C _{oss}		-	70	-	
Reverse Transfer Capacitance	C _{rss}		-	47	-	
Turn-On Delay Time	td _(on)	V _{DD} =-30V, I _D =-1A, V _{GS} =-10V, R _G =6Ω (Note 3)	-	8.4	-	ns
Turn-On Rise Time	t _r		-	30	-	
Turn-Off Delay Time	td _(off)		-	52	-	
Turn-Off Fall Time	t _f		-	16	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I _S	---	-	-	-4.2	A
Diode Forward Voltage	V _{SD}	I _S =-1A, V _{GS} =0V	-	-0.73	-1	V

NOTES :

1. Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$
2. Essentially independent of operating temperature typical characteristics
3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=150^{\circ}\text{C}$. Ratings are based on low frequency and duty cycles to keep initial $T_J=25^{\circ}\text{C}$.
4. The maximum current rating is package limited
5. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper
6. Guaranteed by design, not subject to production testing.

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TYPICAL CHARACTERISTIC CURVES

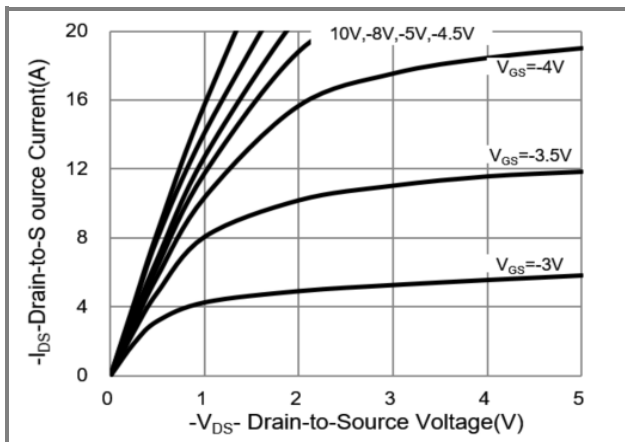


Fig.1 On-Region Characteristics

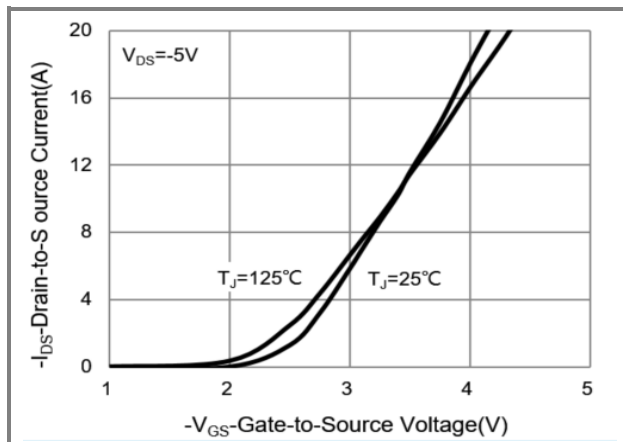


Fig.2 Transfer Characteristics

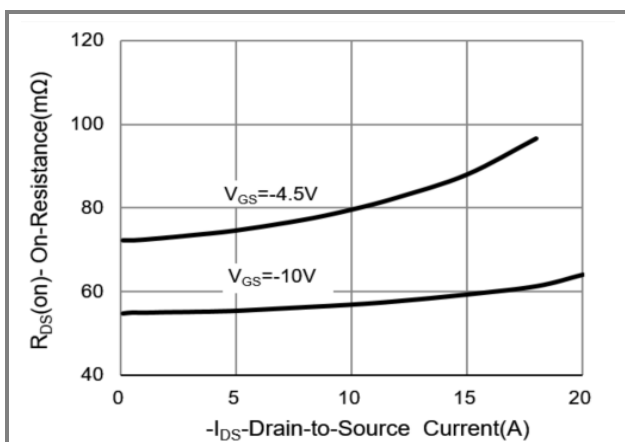


Fig.3 On-Resistance vs. Drain Current

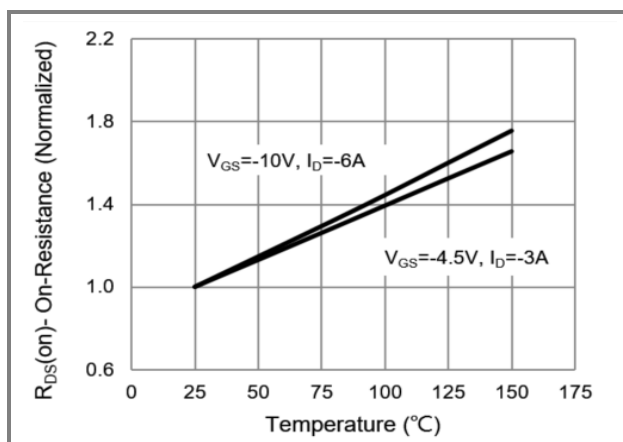


Fig.4 On-Resistance vs. Junction temperature

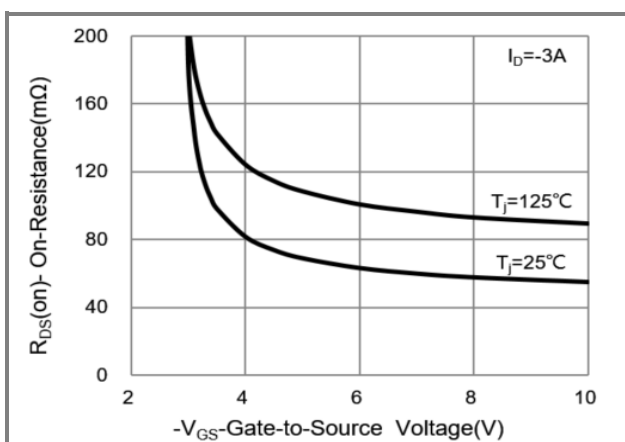


Fig.5 On-Resistance Variation with V_{GS}

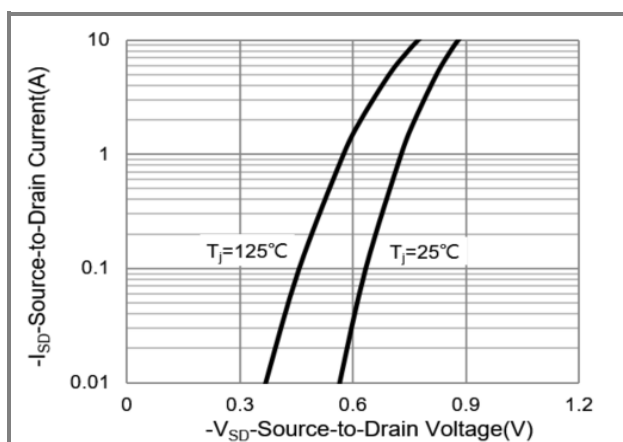


Fig.6 Source-Drain Diode Forward Voltage



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TYPICAL CHARACTERISTIC CURVES

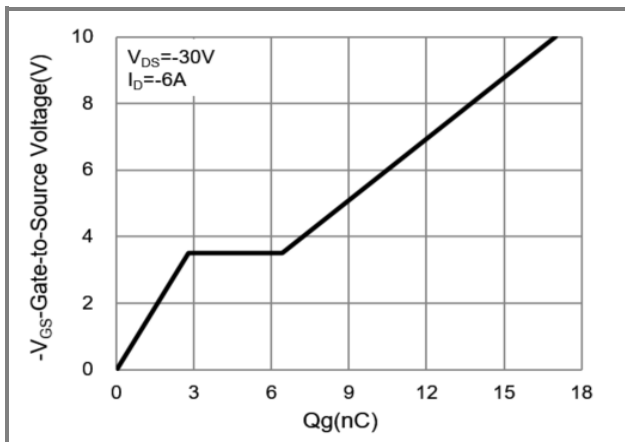


Fig.7 Gate-Charge Characteristics

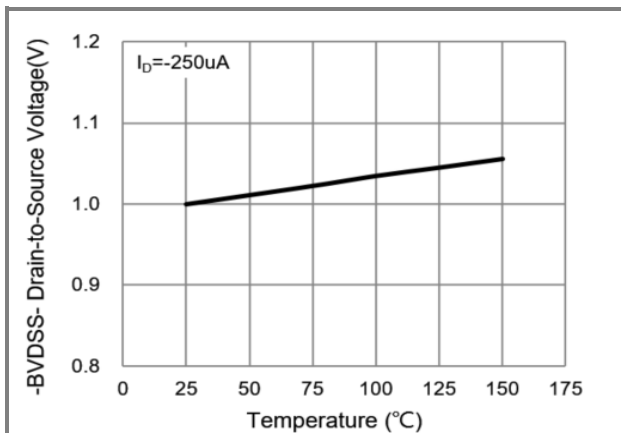


Fig.8 Breakdown Voltage Variation vs. Temperature

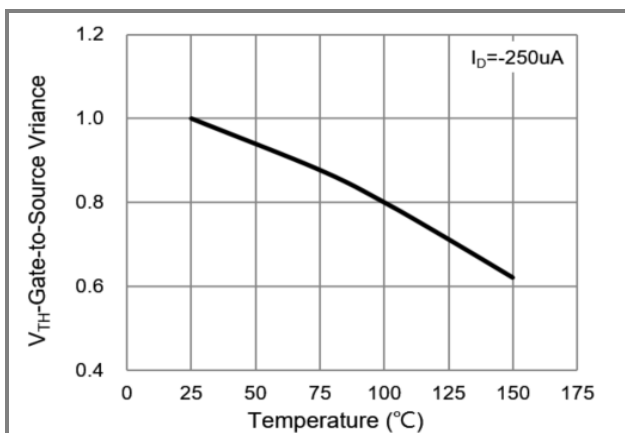


Fig.9 Threshold Voltage Variation with Temperature

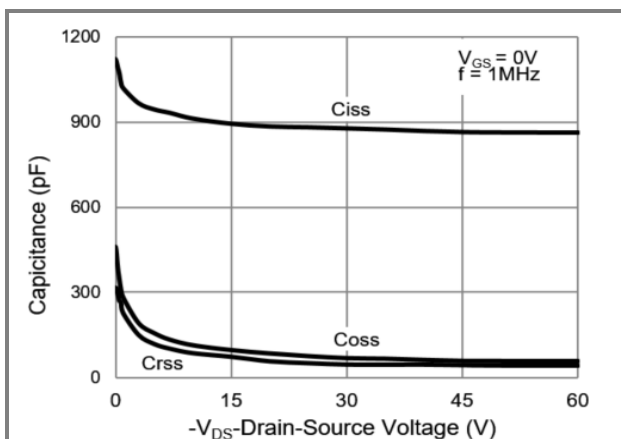


Fig.10 Capacitance vs. Drain-Source Voltage

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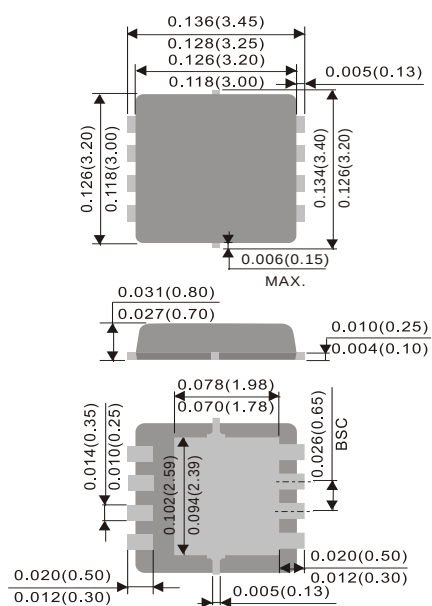
Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJQ4463AP-AU_R2_000A1	DFN3333-8L	5K pcs / 13" reel	4463	Halogen free

Packaging Information & Mounting Pad Layout

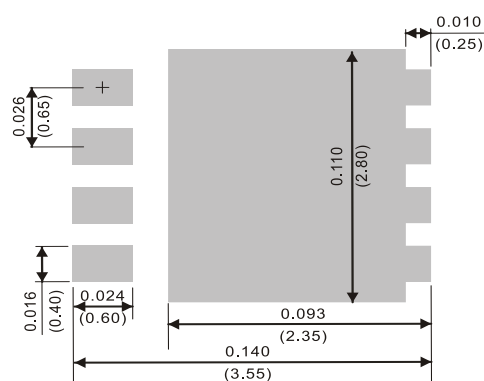
DFN3333-8L Dimension

Unit: inch(mm)



DFN3333-8L Pad Layout

Unit: inch(mm)





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